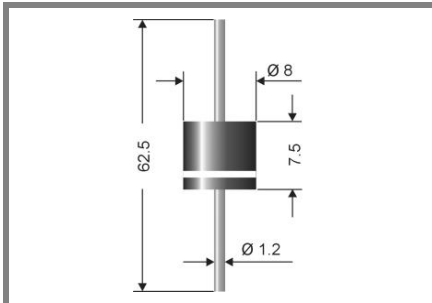


HE6SF 200



Axial lead diode

High efficiency super fast silicon rectifier diode

HE6SF 200

Forward Current: 6 A

Reverse Voltage: 200 to 200 V

Features

- Max. solder temperature: 260°C
- Plastic material has UL classification 94V-0

Mechanical Data

- Plastic case 8 x 7,5 [mm] / P-600 Style
- Weight approx.: 1,5 g
- Terminals: plated terminals solderable per MIL-STD-750
- Mounting position: any
- Standard packaging: 500 pieces per ammo

1) Valid, if leads are kept at ambient temperature at a distance of 10 mm from case

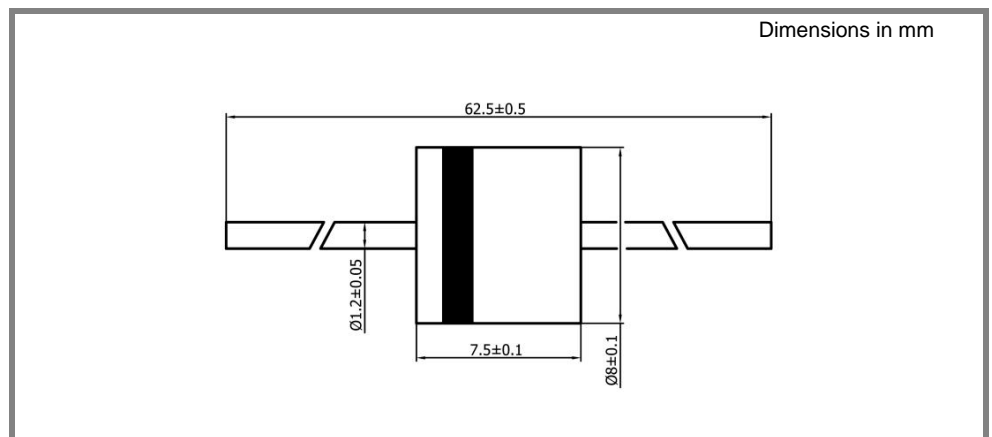
2) $I_F = 5 \text{ A}$, $T_J = 25 \text{ °C}$

3) $T_A = 25 \text{ °C}$

Type	Repetitive peak reverse voltage	Surge peak reverse voltage	Max. reverse recovery time	Max. forward voltage
HE6SF 200	V_{RRM} V 200	V_{RSM} V 200	$I_F = 0,5 \text{ A}$ $I_R = 1 \text{ A}$ $I_{RR} = 0,25 \text{ A}$ t_{rr} ns 200	$V_F^{2)}$ 0,95

Absolute Maximum Ratings		$T_A = 25 \text{ °C}$, unless otherwise specified	
Symbol	Conditions	Values	Units
I_{FAV}	Max. averaged fwd. current, R-load, $T_A = 45 \text{ °C}^1)$	6	A
I_{FRM}	Repetitive peak forward current $f > 15 \text{ Hz}^1)$	60	A
I_{FSM}	Peak forward surge current 50 Hz half sinus-wave $^3)$	300	A
i^2t	Rating for fusing, $t < 10 \text{ ms}^3)$	450	A ² s
R_{thA}	Max. thermal resistance junction to ambient $^1)$	20	K/W
R_{thL}	Max. thermal resistance junction to terminals $^4)$	-	K/W
T_J	Operating junction temperature	-50...+175	°C
T_S	Storage temperature	-50...+175	°C

Characteristics		$T_A = 25 \text{ °C}$, unless otherwise specified	
Symbol	Conditions	Values	Units
I_R	Maximum leakage current, $T_J = 25 \text{ °C}$; $V_R = V_{RRM}$	<25	µA
	$T_J = \text{°C}$; $V_R = V_{RRM}$		
C_J	Typical junction capacitance (at MHz and applied reverse voltage of V)	-	pF
Q_{rr}	Reverse recovery charge ($U_R = V$; $I_F = A$; $dI_F/dt = A/ms$)	-	µC
E_{RSM}	Non repetitive peak reverse avalanche energy ($I_R = mA$; $T_J = \text{°C}$; inductive load switched off)	-	mJ



case: 8 x 7,5 [mm]

